

## IPD038N04NGBTMA1

### IPD038N04NGBTMA1 Information



For Reference Only

Part Number IPD038N04NGBTMA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 40V 90A TO252-3 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# IPD038N04NGBTMA1 Specifications

Manufacturer Part Number         IPD038N04NGBTMA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-252-3, DPak (2 Leads + Tab), SC-63           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         90A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 45μA           Gate Charge (Qg) (Max) @ Vgs         56nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4500pF @ 20V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         94W (Tc)           Rds On (Max) @ Id, Vgs         3.8 mOhm @ 90A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-T0252-3           Package / Case         TO-252-3, DPak (2 Leads + Tab), SC-63           Report errors?		
Category         Discrete Semiconductor Products           Fackage         Transistors - FETs, MOSFETs - Single           Package         TO-252-3, DPak (2 Leads + Tab), SC-63           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         90A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 45µA           Gate Charge (Qg) (Max) @ Vgs         56nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4500pF @ 20V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         94W (Tc)           Rds On (Max) @ Id, Vgs         3.8 mOhm @ 90A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-TO252-3           Package / Case         TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IPD038N04NGBTMA1
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FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  40V  Current - Continuous Drain (Id) @ 25°C  Prive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Jenuary Surface Mount  Supplier Device Package  PG-TO252-3  Package / Case  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  40V  40V  40V  40V  40V  40V  45V  45V	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C90A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 45μAGate Charge (Qg) (Max) @ Vgs56nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4500pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)94W (Tc)Rds On (Max) @ Id, Vgs3.8 mOhm @ 90A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	OptiMOS?
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Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4500pF @ 20V  Vgs (Max)  ±20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  3.8 mOhm @ 90A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  PG-TO252-3  Package / Case  TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
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	Supplier Device Package	PG-TO252-3
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

#### IPD038N04NGBTMA1 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPD038N04NGBTMA1 Payment Methods



















## IPD038N04NGBTMA1 Shipping Methods













If you have any question about IPD038N04NGBTMA1, please do not hesitate to contact us!

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